

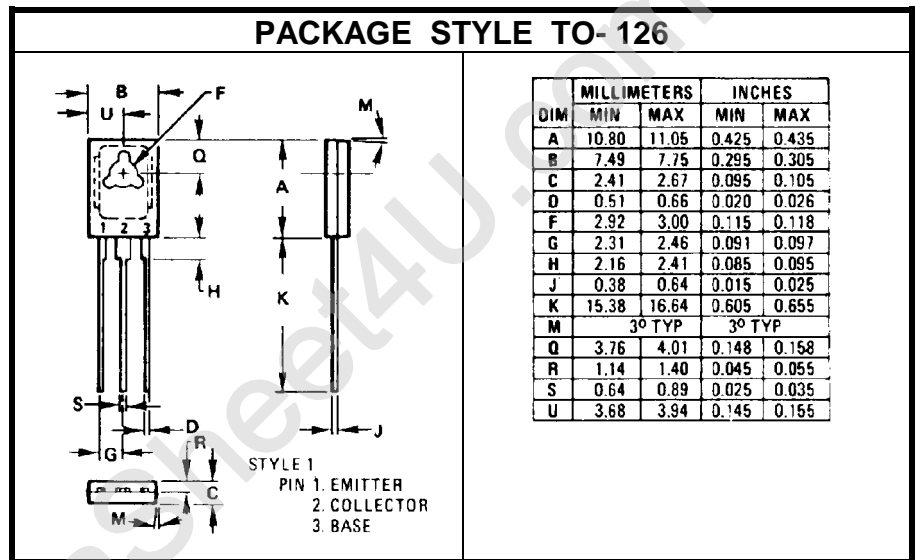
# NPN SILICON HIGH FREQUENCY TRANSISTOR

## DESCRIPTION:

The **ASI BFT51F.A** is Designed for High Frequency Amplifier Applications.

## MAXIMUM RATINGS

$I_C$	500 mA
$V_{CE}$	20 V
$P_{DISS}$	3.0 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+175^\circ C$
$T_{STG}$	$-65^\circ C$ to $+175^\circ C$
$\theta_{JC}$	$50^\circ C/W$



## CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 5.0$ mA	10			V
$BV_{CER}$	$I_C = 1.0$ mA $R_{BE} = 100 \Omega$	18			V
$BV_{CBO}$	$I_C = 1.0$ mA	20			V
$I_{CEO}$	$V_{CE} = 5.0$ V			1.0	mA
$I_{CES}$	$V_{CE} = 10$ V			100	$\mu A$
$I_{EBO}$	$V_{EB} = 3.0$ V			1.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 100$ mA $I_C = 300$ mA	40			---
$f_t$	$V_{CE} = 5.0$ V $I_C = 300$ mA $f = 100$ MHz	1.0	2.0		GHz
$C_{ob}$	$V_{CB} = 5.0$ V $f = 1.0$ MHz		4.0		pF